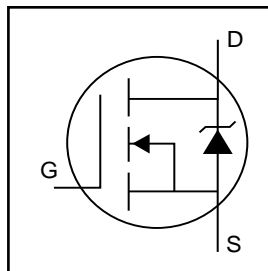


- Surface Mount
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- Fast Switching
- Fully Avalanche Rated

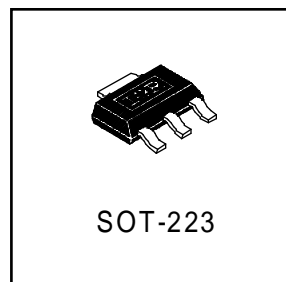


| |
|---------------------------|
| $V_{DSS} = 55V$ |
| $R_{DS(on)} = 0.14\Omega$ |
| $I_D = 2.0A$ |

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SOT-223 package is designed for surface-mount using vapor phase, infra red, or wave soldering techniques. Its unique package design allows for easy automatic pick-and-place as with other SOT or SOIC packages but has the added advantage of improved thermal performance due to an enlarged tab for heatsinking. Power dissipation of 1.0W is possible in a typical surface mount application.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|--------------------------|---|-------------|-------|
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^{**}$ | 2.8 | A |
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^*$ | 2.0 | |
| $I_D @ T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^*$ | 1.6 | |
| I_{DM} | Pulsed Drain Current ① | 16 | |
| $P_D @ T_A = 25^\circ C$ | Power Dissipation (PCB Mount)** | 2.1 | W |
| $P_D @ T_A = 25^\circ C$ | Power Dissipation (PCB Mount)* | 1.0 | W |
| | Linear Derating Factor (PCB Mount)* | 8.3 | mW/°C |
| V_{GS} | Gate-to-Source Voltage | ± 16 | V |
| E_{AS} | Single Pulse Avalanche Energy② | 32 | mJ |
| I_{AR} | Avalanche Current① | 2.0 | A |
| E_{AR} | Repetitive Avalanche Energy①* | 0.1 | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | 7.2 | V/ns |
| T_J, T_{STG} | Junction and Storage Temperature Range | -55 to +150 | °C |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|--|------|------|-------|
| $R_{\theta JA}$ | Junction-to-Amb. (PCB Mount, steady state)* | 90 | 120 | °C/W |
| $R_{\theta JA}$ | Junction-to-Amb. (PCB Mount, steady state)** | 50 | 60 | |

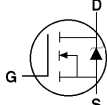
* When mounted on FR-4 board using minimum recommended footprint.

** When mounted on 1 inch square copper board, for comparison with other SMD devices.

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|--------------------------------------|------|-------|------|----------|--|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 55 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.015 | — | V/°C | Reference to $25^\circ\text{C}, I_D = 1mA$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | — | 0.14 | Ω | $V_{GS} = 10V, I_D = 2.0A$ ④ |
| | | — | — | 0.20 | | $V_{GS} = 5.0V, I_D = 1.2A$ ④ |
| | | — | — | 0.28 | | $V_{GS} = 4.0V, I_D = 1.0A$ ④ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 1.0 | — | 2.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| g_{fs} | Forward Transconductance | 2.3 | — | — | S | $V_{DS} = 25V, I_D = 1.0A$ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | 25 | μA | $V_{DS} = 55V, V_{GS} = 0V$ |
| | | — | — | 250 | | $V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | $V_{GS} = 16V$ |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | $V_{GS} = -16V$ |
| Q_g | Total Gate Charge | — | 9.5 | 14 | nC | $I_D = 2.0A$ |
| Q_{gs} | Gate-to-Source Charge | — | 1.1 | 1.7 | | $V_{DS} = 44V$ |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | — | 3.0 | 4.4 | | $V_{GS} = 10V$, See Fig. 6 and 9 ④ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 5.1 | — | ns | $V_{DD} = 28V$ |
| t_r | Rise Time | — | 4.9 | — | | $I_D = 2.0A$ |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 14 | — | | $R_G = 6.0\Omega$ |
| t_f | Fall Time | — | 2.9 | — | | $R_D = 14\Omega$, See Fig. 10 ④ |
| C_{iss} | Input Capacitance | — | 230 | — | pF | $V_{GS} = 0V$ |
| C_{oss} | Output Capacitance | — | 66 | — | | $V_{DS} = 25V$ |
| C_{rss} | Reverse Transfer Capacitance | — | 30 | — | | $f = 1.0MHz$, See Fig. 5 |

Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|---|---|------|------|-------|--|
| I_S | Continuous Source Current (Body Diode) | — | — | 1.3 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I_{SM} | Pulsed Source Current (Body Diode) ① | — | — | 16 | | |
| V_{SD} | Diode Forward Voltage | — | — | 1.0 | V | $T_J = 25^\circ\text{C}, I_S = 2.0A, V_{GS} = 0V$ ④ |
| t_{rr} | Reverse Recovery Time | — | 41 | 61 | ns | $T_J = 25^\circ\text{C}, I_F = 2.0A$ |
| Q_{rr} | Reverse Recovery Charge | — | 73 | 110 | nC | $di/dt = 100A/\mu s$ ④ |
| t_{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$) | | | | |

Specification changes

| Rev. # | Parameters | Old spec. | New spec. | Comments | Effective Date |
|--------|-----------------|-----------|-----------|--------------------------------------|----------------|
| 1 | V_{GS} (Max.) | ± 20 | ± 16 | Decrease V_{GS} Max. Specification | 10/7/96 |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 4.0mH$
 $R_G = 25\Omega, I_{AS} = 4.0A$. (See Figure 12)
- ③ $I_{SD} \leq 2.0A, di/dt \leq 170A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

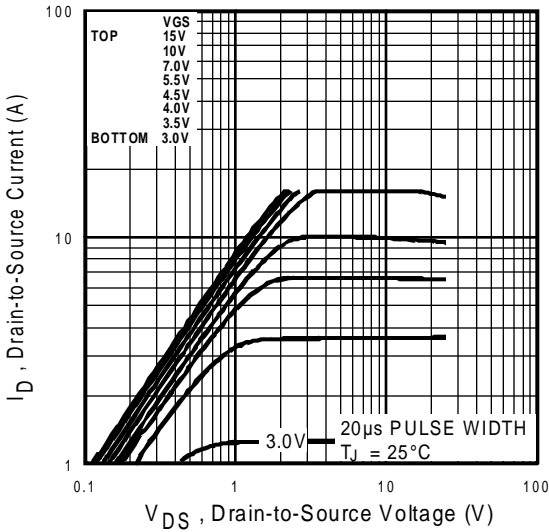


Fig 1. Typical Output Characteristics,
 $T_J = 25^\circ\text{C}$

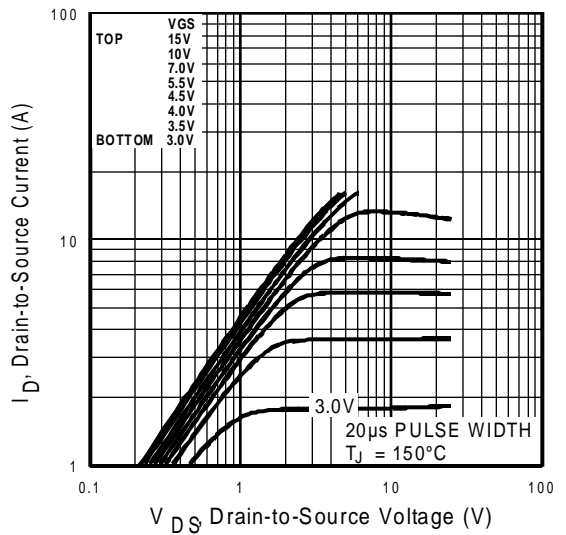


Fig 2. Typical Output Characteristics,
 $T_J = 150^\circ\text{C}$

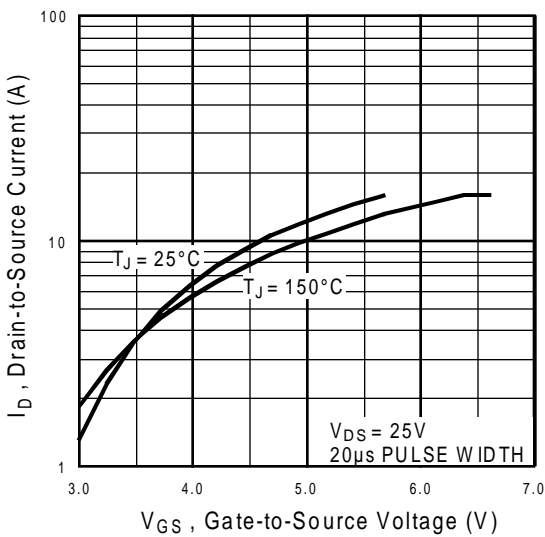


Fig 3. Typical Transfer Characteristics

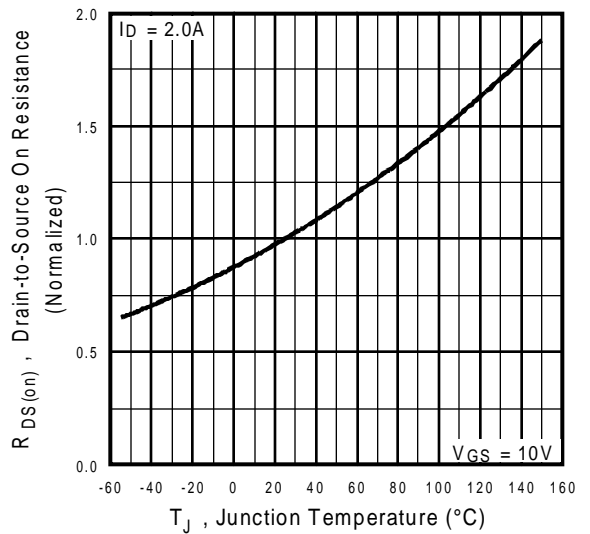


Fig 4. Normalized On-Resistance
 Vs. Temperature

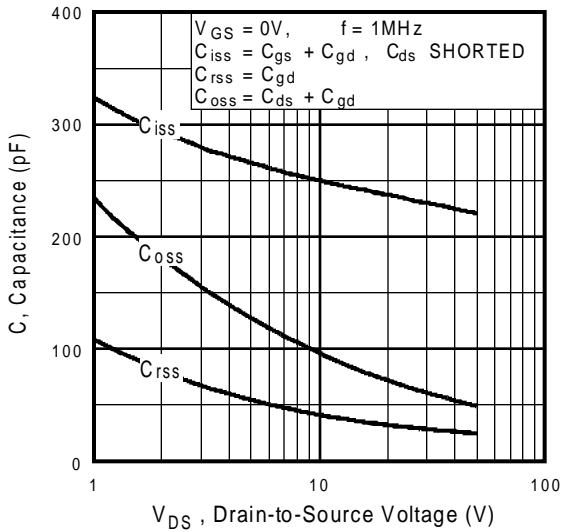


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

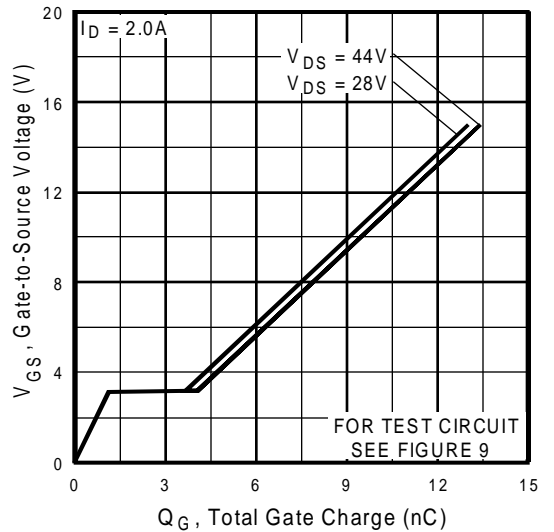


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

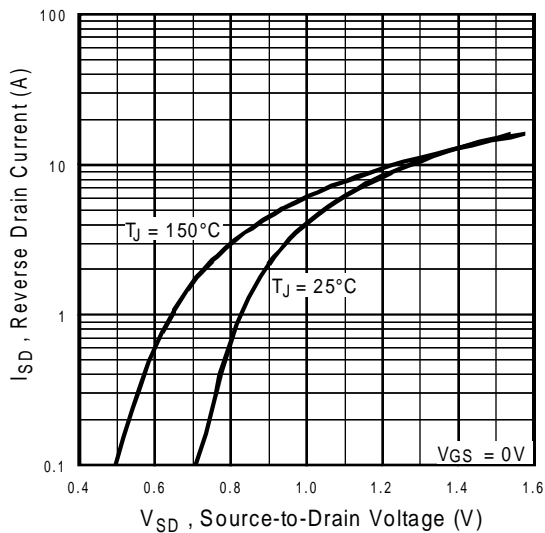


Fig 7. Typical Source-Drain Diode Forward Voltage

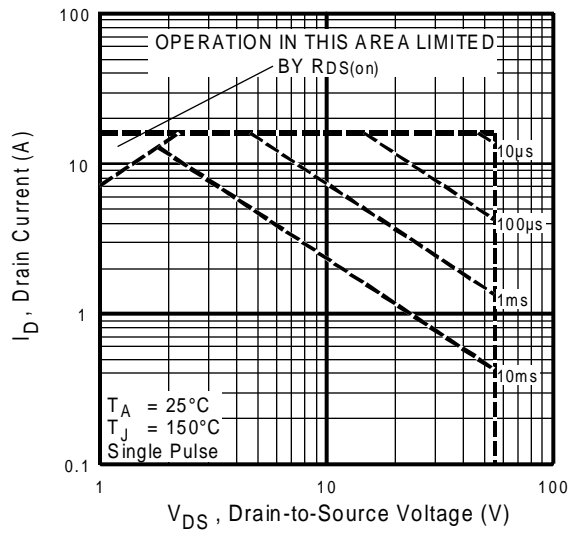


Fig 8. Maximum Safe Operating Area

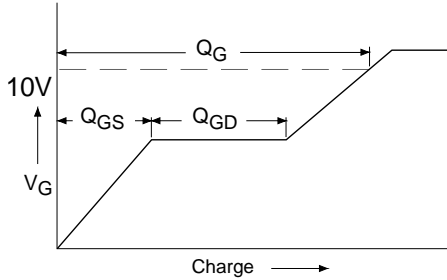


Fig 9a. Basic Gate Charge Waveform

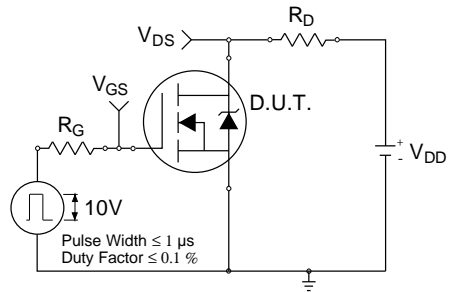


Fig 10a. Switching Time Test Circuit

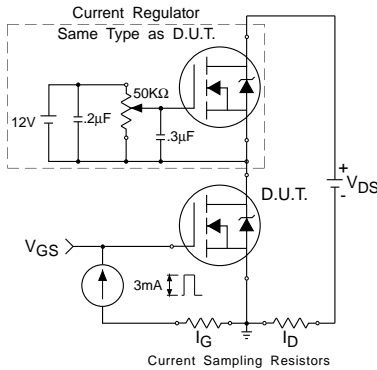


Fig 9b. Gate Charge Test Circuit

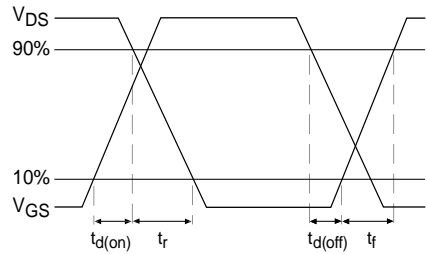


Fig 10b. Switching Time Waveforms

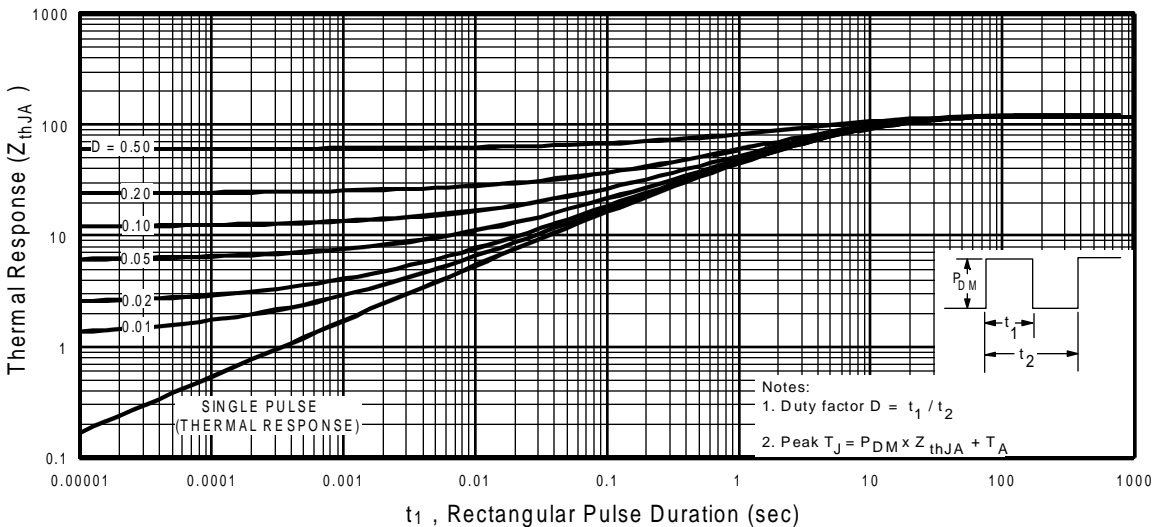


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

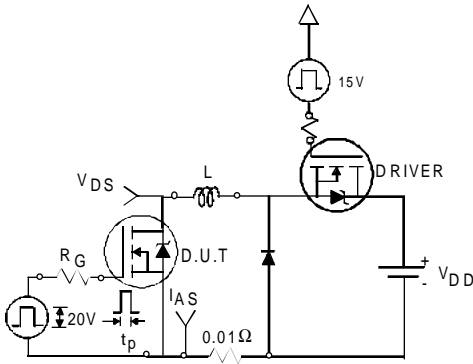


Fig 12a. Unclamped Inductive Test Circuit

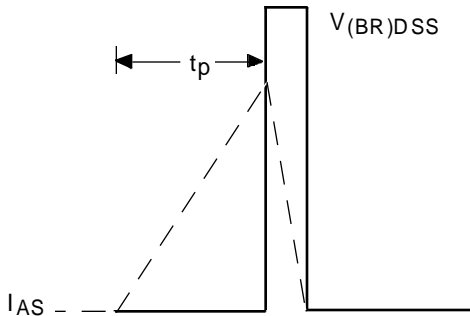


Fig 12b. Unclamped Inductive Waveforms

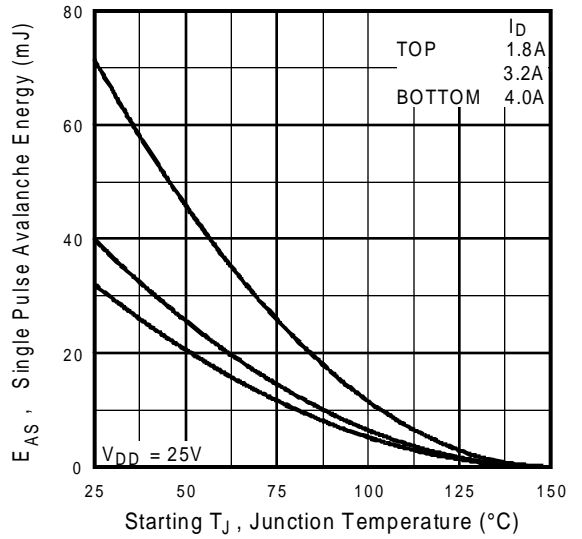
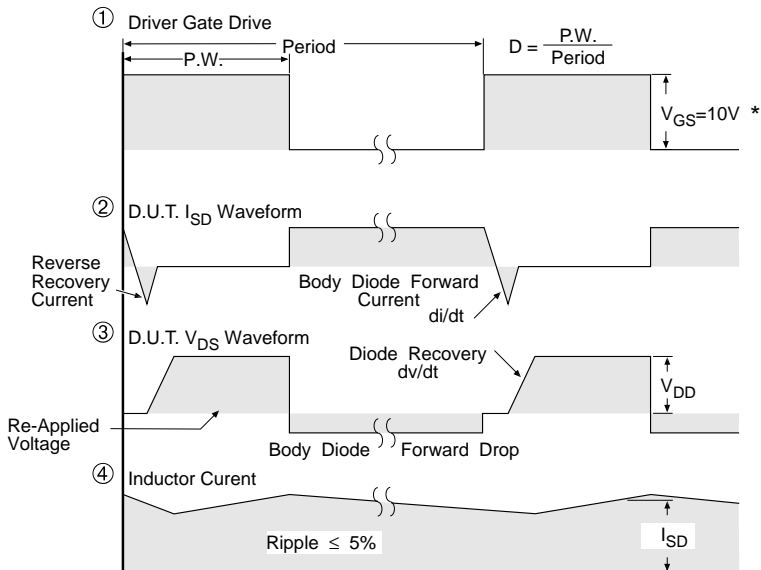
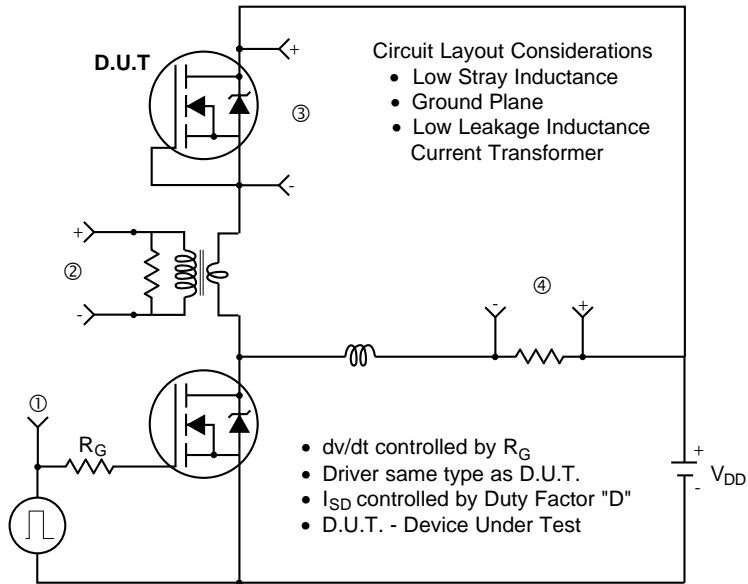


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

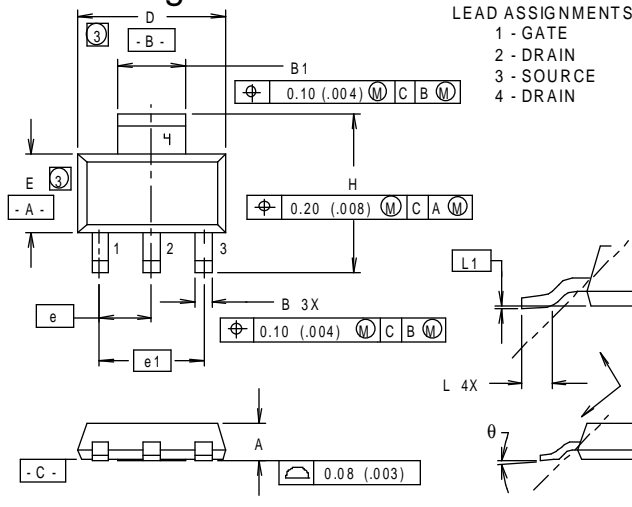
Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

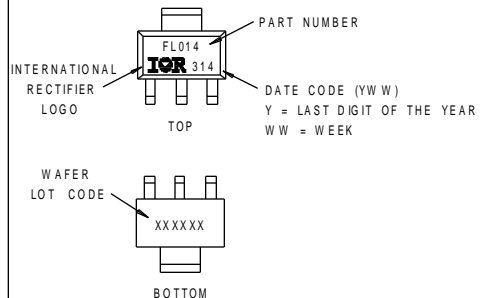
Fig 13. For N-Channel HEXFETS

SOT-223 Package Details



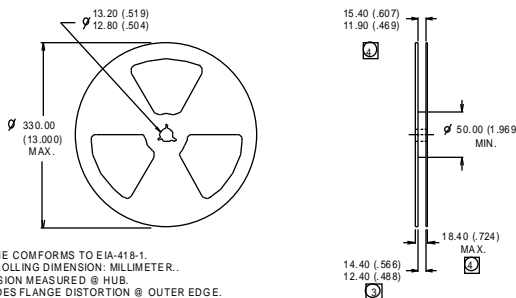
| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|------|
| | MIN | MAX | MIN | MAX |
| A | 1.55 | 1.80 | .061 | .071 |
| B | 0.65 | 0.85 | .026 | .033 |
| B1 | 2.95 | 3.15 | .116 | .124 |
| C | 0.25 | 0.35 | .010 | .014 |
| D | 6.30 | 6.70 | .248 | .264 |
| E | 3.30 | 3.70 | .130 | .146 |
| e | 2.30 BSC | | .0905 BSC | |
| e1 | 4.60 BSC | | .181 BSC | |
| H | 6.71 | 7.29 | .267 | .284 |
| L | 0.91 | --- | .036 | --- |
| L1 | 0.061 BSC | | .0024 BSC | |
| θ | --- | 10° | --- | 10° |

Part Marking (IRFL014 example)



Tape & Reel

- NOTES:
 1. CONTROLLING DIMENSION: MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.
 3. EACH \varnothing 330.00 (13.000) REEL CONTAINS 2,500 DEVICES.



WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 3-30-4 Nishi-Ikeburo 3-Home, Toshima-Ki, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

<http://www.irf.com/>

Data and specifications subject to change without notice.

10/96